30V N-Channel NexFET™ Power MOSFET

Check for Samples: CSD17312Q5

FEATURES

- **Optimized for 5V Gate Drive**
- **Ultra Low Q_g and Q_{gd}**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 5-mm × 6-mm Plastic Package**

APPLICATIONS

- **Notebook Point-of-Load**
- **Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30		V
Q_g	Gate Charge Total (4.5V)	28		nC
Q_{gd}	Gate Charge Gate to Drain	6		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V	1.8	mΩ
		V_{GS} = 4.5V	1.4	mΩ
		V_{GS} = 8V	1.2	mΩ
$V_{GS(th)}$	Threshold Voltage	1.1		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17312Q5	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

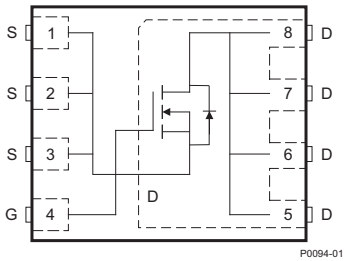
ABSOLUTE MAXIMUM RATINGS

T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / –8	V
I_D	Continuous Drain Current, T_C = 25°C	100	A
	Continuous Drain Current(1)	38	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	200	A
P_D	Power Dissipation(1)	3.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, Single Pulse I_D = 130A, L = 0.1mH, R_G = 25Ω	845	mJ

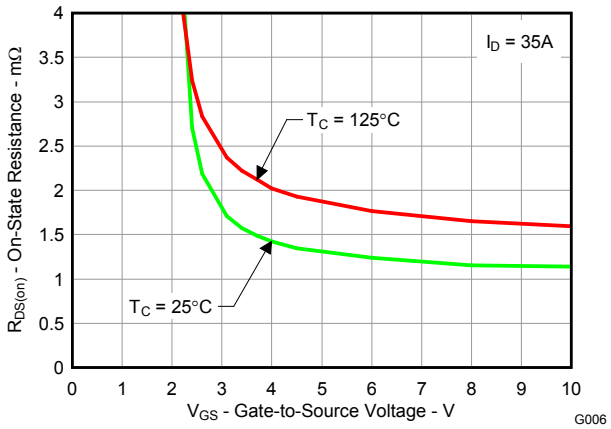
(1) Typical $R_{\theta JA}$ = 39°C/W when mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%

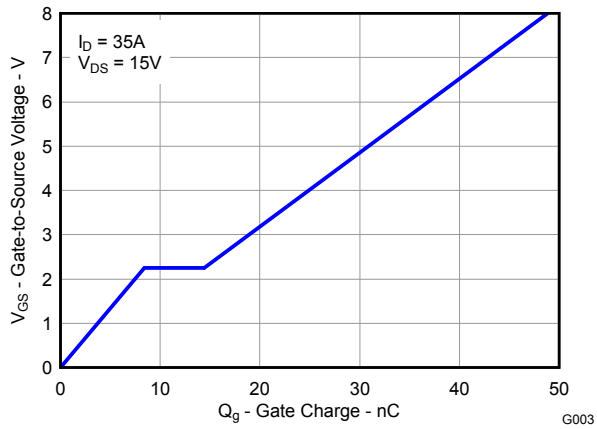
Top View



$R_{DS(on)}$ vs V_{GS}



GATE CHARGE



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

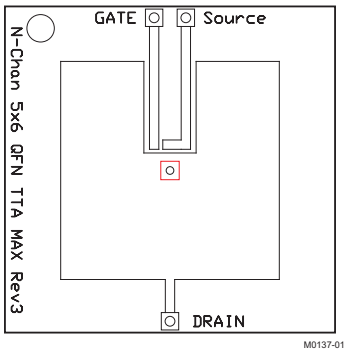
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250μA	30			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 24V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = +10/–8V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.9	1.1	1.5	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V, I_D = 35A		1.8	2.4	mΩ
		V_{GS} = 4.5V, I_D = 35A		1.4	1.7	mΩ
		V_{GS} = 8V, I_D = 35A		1.2	1.5	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 35A		200		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		4030	5240	pF
C_{oss}	Output Capacitance			2220	2890	pF
C_{rss}	Reverse Transfer Capacitance			93	120	pF
R_G	Series Gate Resistance			1.1	2.2	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 15V, I_{DS} = 35A		28	36	nC
Q_{gd}	Gate Charge Gate to Drain			6		nC
Q_{gs}	Gate Charge Gate to Source			8.4		nC
$Q_{g(th)}$	Gate Charge at Vth			4.4		nC
Q_{oss}	Output Charge	V_{DS} = 14.8V, V_{GS} = 0V		57		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 35A, R_G = 2Ω		9.5		ns
t_r	Rise Time			27		ns
$t_{d(off)}$	Turn Off Delay Time			35		ns
t_f	Fall Time			23		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = 35A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = 14.8V, I_F = 35A, di/dt = 300A/μs		88		nC
t_{rr}	Reverse Recovery Time			43		ns

THERMAL CHARACTERISTICS

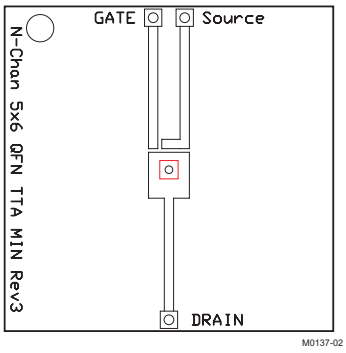
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			49	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 49°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 119°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

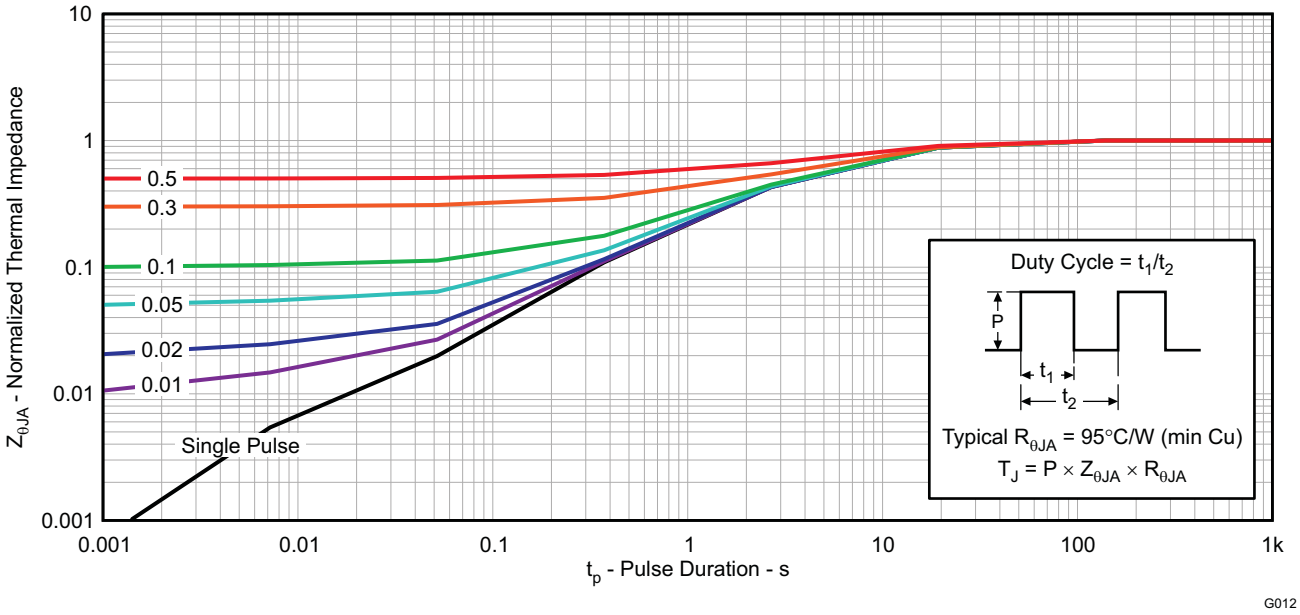


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

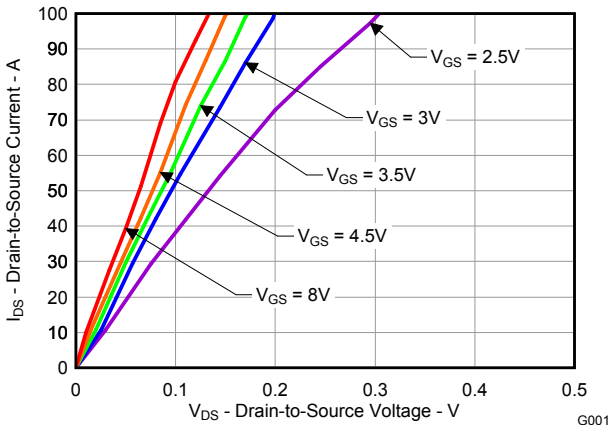


Figure 2. Saturation Characteristics

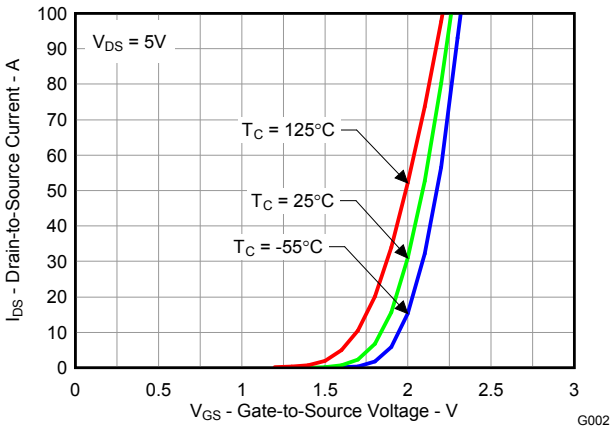


Figure 3. Transfer Characteristics

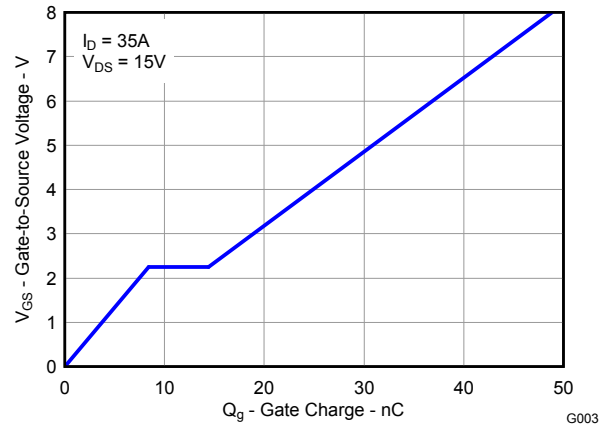


Figure 4. Gate Charge

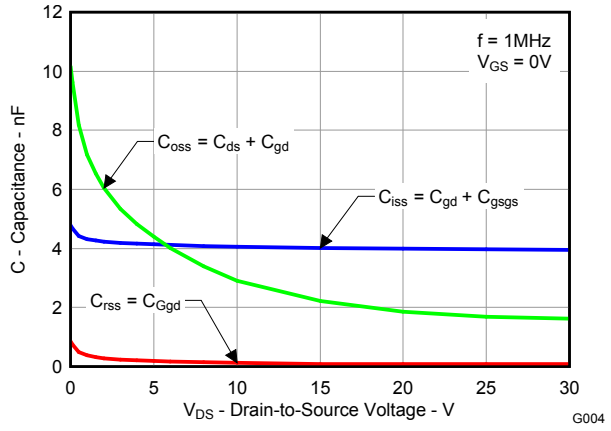


Figure 5. Capacitance

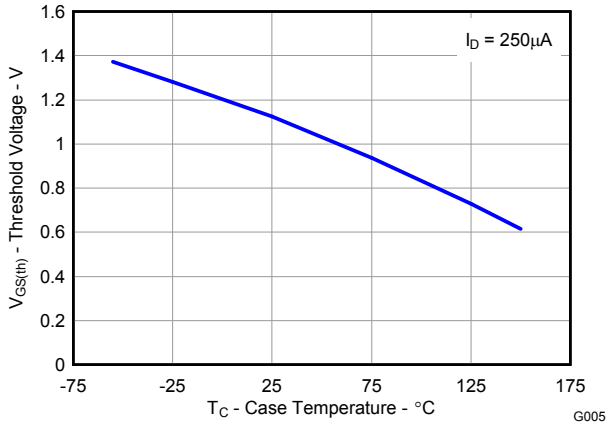


Figure 6. Threshold Voltage vs. Temperature

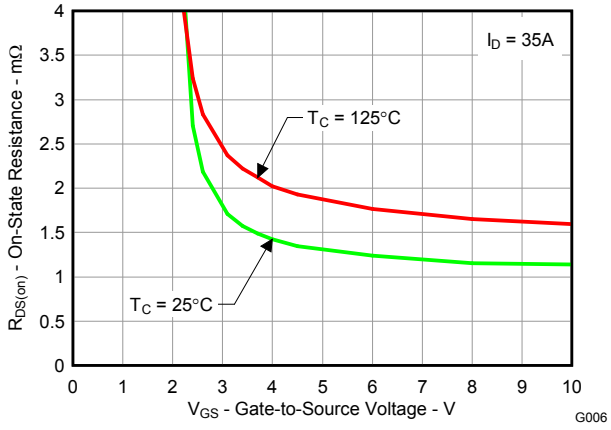


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

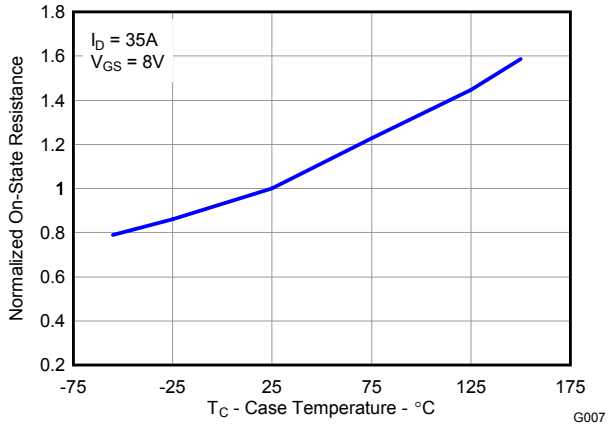


Figure 8. Normalized On-State Resistance vs. Temperature

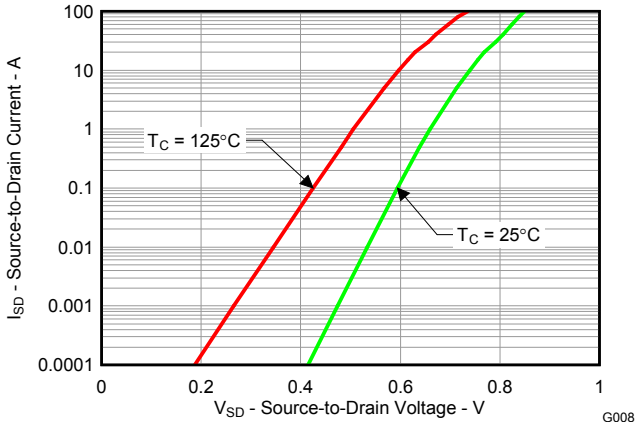


Figure 9. Typical Diode Forward Voltage

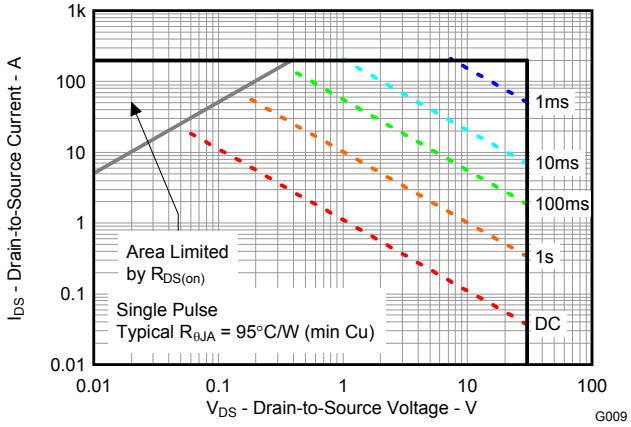


Figure 10. Maximum Safe Operating Area

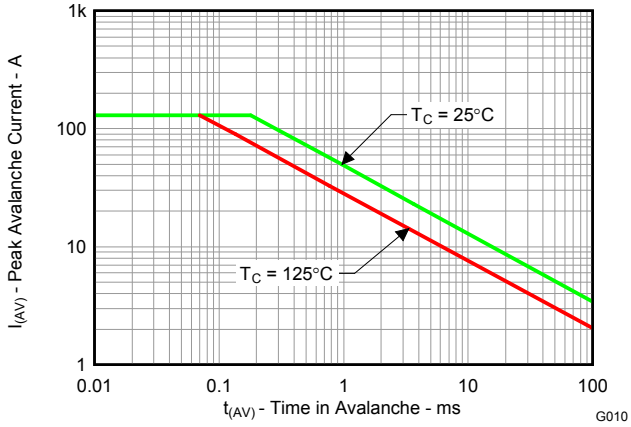


Figure 11. Single Pulse Unclamped Inductive Switching

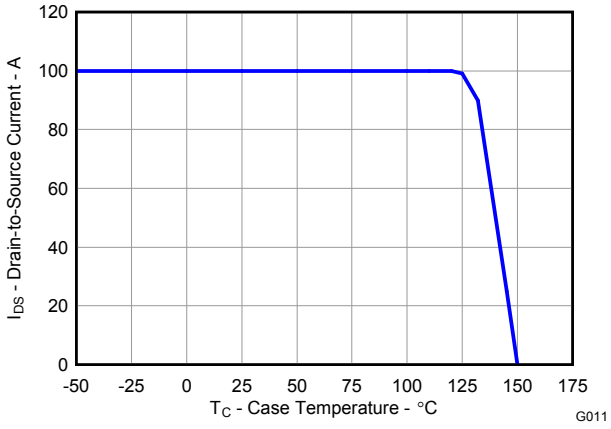
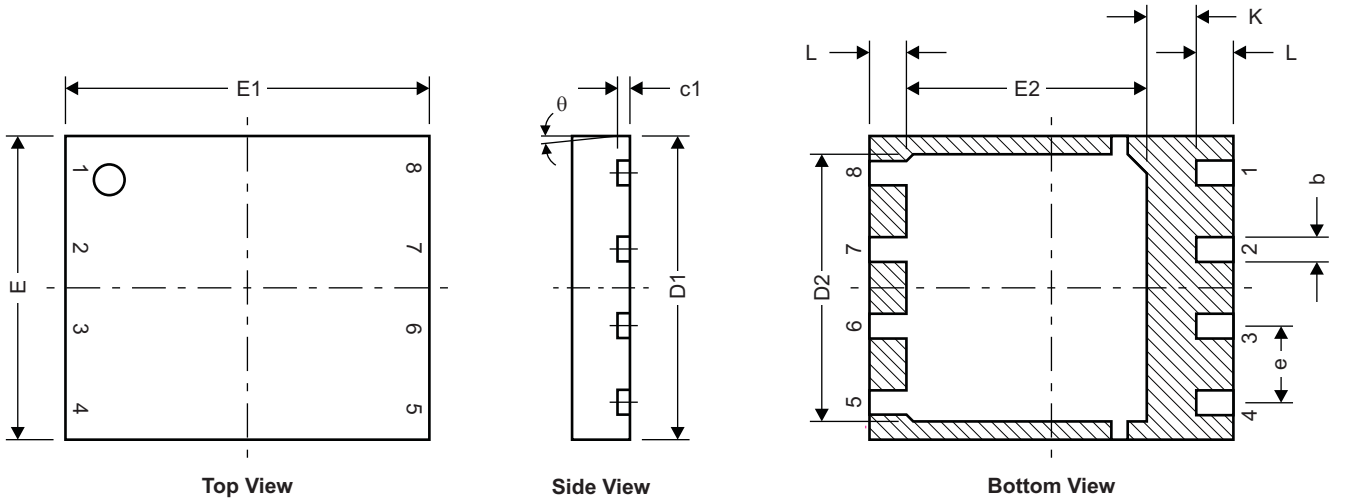
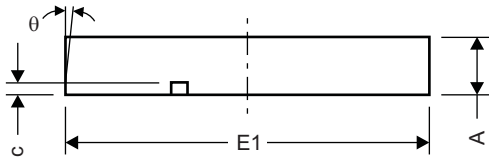


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q5 Package Dimensions

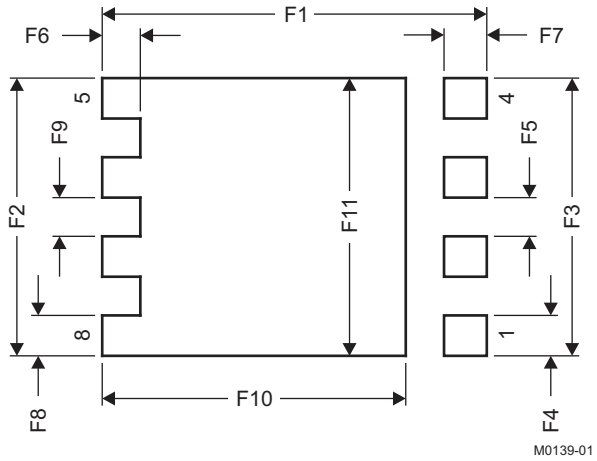




M0140-01

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

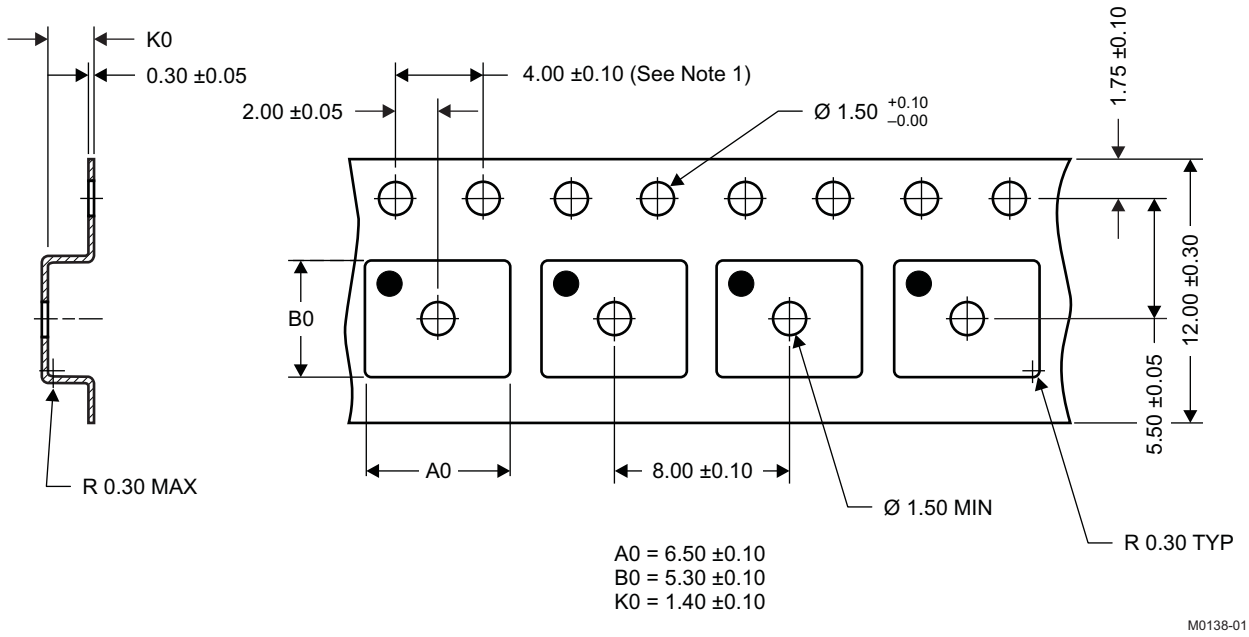
Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5 Tape and Reel Information



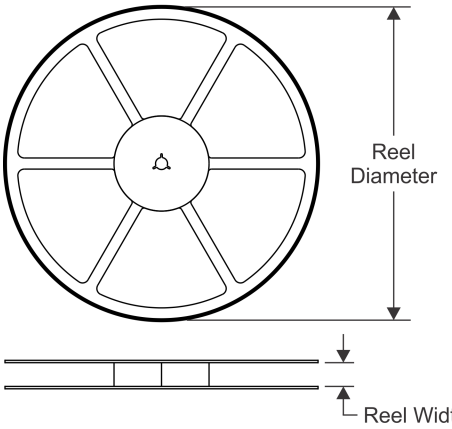
Notes:
1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm, unless otherwise specified.
5. Thickness: 0.30 ±0.05mm
6. MSL1 260°C (IR and convection) PbF reflow compatible

REVISION HISTORY

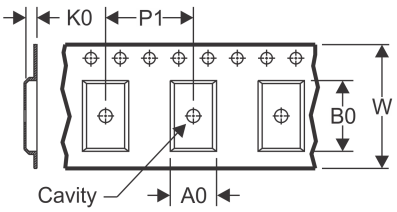
Changes from Original (March 2010) to Revision A	Page
• Deleted the Package Marking Information section	7

TAPE AND REEL INFORMATION

REEL DIMENSIONS

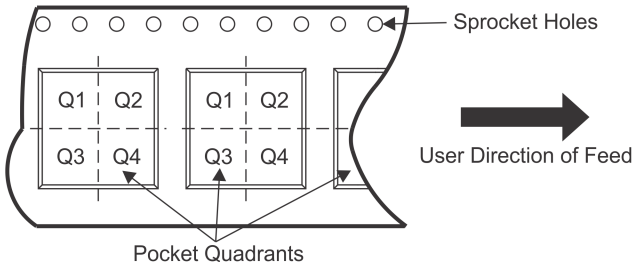


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

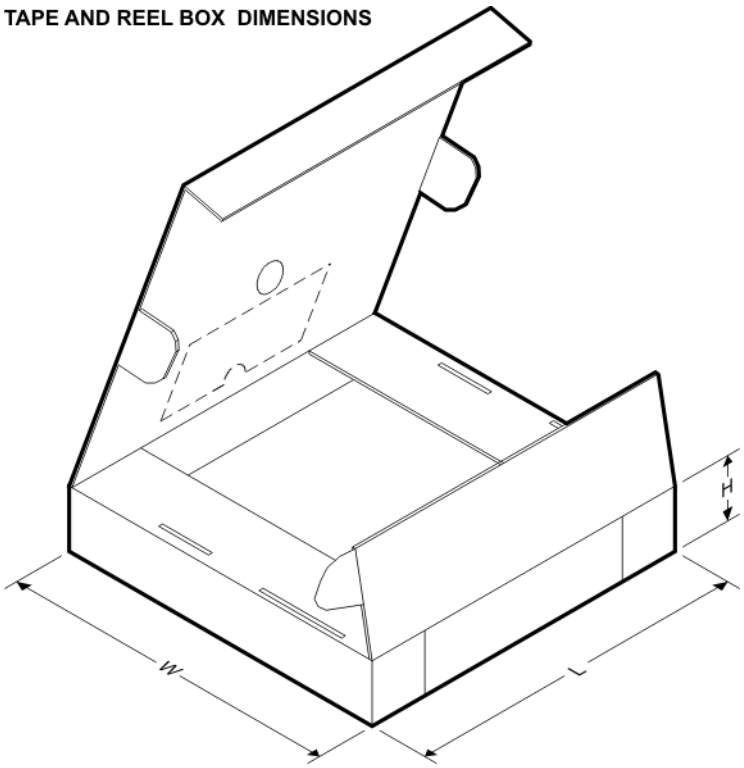
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17312Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17312Q5	SON	DQH	8	2500	335.0	335.0	32.0

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